# VS-8ETH06HN3

**Vishay Semiconductors** 

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# Hyperfast Rectifier, 8 A FRED Pt<sup>®</sup> FEATURES



## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub>	8 A								
V <sub>R</sub>	600 V								
V <sub>F</sub> at I <sub>F</sub>	1.3 V								
t <sub>rr</sub> typ.	18 ns								
T <sub>J</sub> max.	175 °C								
Package	TO-220AC								
Circuit configuration	Single								

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test



- RoHS COMPLIANT HALOGEN FREE
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

## **MECHANICAL DATA**

### Case: TO-220AC

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	8							
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	А						
Repetitive peak forward current	I <sub>FM</sub>		16							
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μΑ	600	-	-	V				
Forward voltage V <sub>F</sub>		I <sub>F</sub> = 8 A	-	2.0	2.4	V				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8					
Reverse leakage current		$V_R = V_R$ rated	-	0.03	50					
neverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	55	500	μA				
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF				
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS				
		I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = 1	00 A/µs, V <sub>R</sub> = 30 V	-	18	-					
Reverse recovery time	+	$I_F = 8 A, dI_F/dt = 1$	100 A/µs, V <sub>R</sub> = 30 V	-	20	-	20				
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	A				
		T <sub>J</sub> = 125 °C	l <sub>F</sub> = 8 A dl <sub>F</sub> /dt = 200 A/μs	-	40	-					
Peak recovery current		T <sub>J</sub> = 25 °C		-	2.4	-					
Feak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm B} = 390 \text{ V}$	-	4.8	-	~				
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	25	-	nC				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	no				
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns				
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 600 A/µs	-	12	-	А				
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	220	-	nC				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	PARAMETER SYMBOL		MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C				
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.4	2					
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-					
Waiaht			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC	8ETH06H							

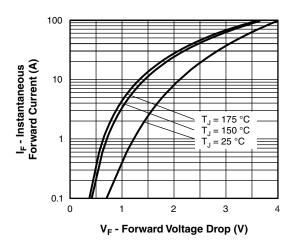
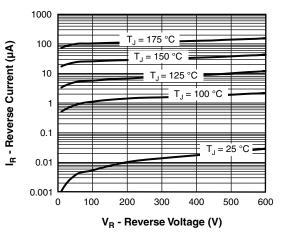
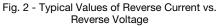


Fig. 1 - Typical Forward Voltage Drop Characteristics





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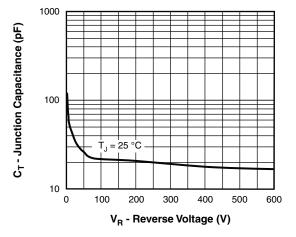


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

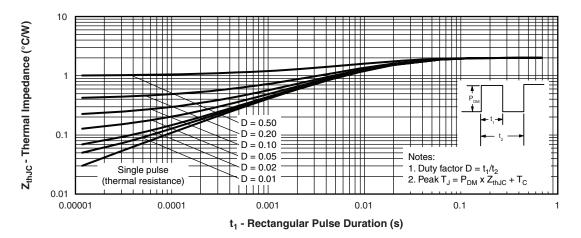
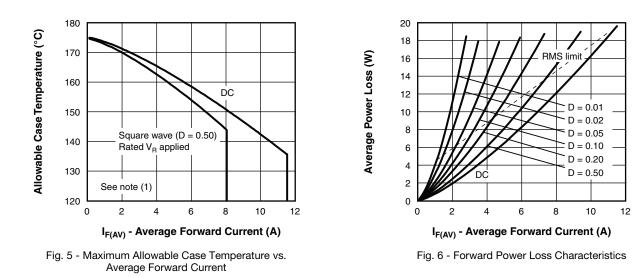


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



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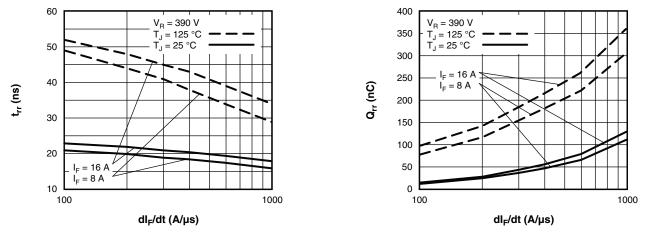


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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#### Note

SHA

(1) Formula Pd<sub>REV</sub>) (Pd R<sub>thJC</sub>; used:  $\mathsf{T}_\mathsf{C}$ TJ + х Pd Forward power loss = I<sub>F(AV)</sub> х  $V_{FM}$ at  $(I_{F(AV)}/D)$ (see fig. 8); =  $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$ 

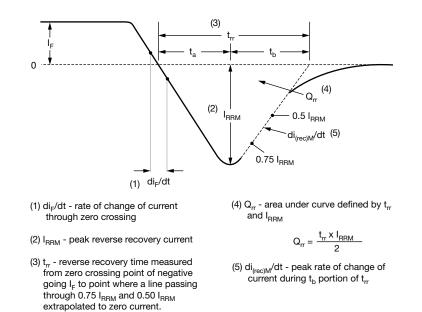


Fig. 9 - Reverse Recovery Waveform and Definitions





## **ORDERING INFORMATION TABLE**

Device code	VS-	8	Е	т	н	06	н	N3
		(2)	(3)	4	(5)	(6)	(7)	(8)
	<u>ر</u>	Vick		niconduc	tore pro	duct	U	U
	2 -			ng (8 = $8$		Juuci		
	3 -		single d	•	,			
	4 -	T =	TO-220	, D <sup>2</sup> PAk	(			
	5 -	H =	hyperfa	st recov	ery			
	6 -	Volt	age rati	ng (06 =	: 600 V)			
	7 -	H =	AEC-Q	101 qua	lified			
	8 -	Env	ironmer	ntal digit:	:			
		N3 :	= haloge	en-free,	RoHS-c	ompliar	nt, and t	otally le

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-8ETH06HN3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions TO-220AC www.vishay.com/doc?95221								
Part marking information	TO-220ACHN3	www.vishay.com/doc?95068						



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**TO-220AC** 

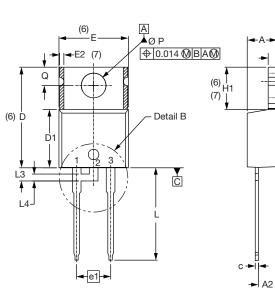
B Seating

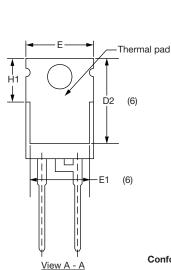
A-

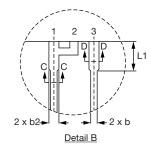
-A1

plane

## **DIMENSIONS** in millimeters and inches









Conforms to JEDEC<sup>®</sup> outline TO-220AC

⊕ 0.015 BA

SYMBOL	MILLIM	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		L3	1.78	2.13	0.070	0.084	
с	0.36	0.61	0.014	0.024			L4	0.76	1.27	0.030	0.050	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.73	0.139	0.147	
D	14.85	15.25	0.585	0.600	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- (4) Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimension: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

<sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

<sup>(8)</sup> Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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